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semiconductor substrate, wherein the silicide strap comprises a refractory metal layer reacted with semiconductor material in the conductive element, the dielectric spacer and the semiconductor substrate.

Add new Claims 16-25 as follows:

-- 16. The semiconductor structure of Claim 8, wherein the semiconductor material comprises amorphous silicon.

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17. The semiconductor structure of Claim 8, wherein upper surfaces of the conductive element, the sidewall spacer and the semiconductor substrate comprise an implanted semiconductor layer.

18. The semiconductor structure of Claim 17, wherein the implanted semiconductor layer comprises silicon.

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19. A semiconductor structure comprising:
a semiconductor substrate;
a conductive element located over the semiconductor substrate;
a dielectric spacer located adjacent to a sidewall of the conductive element; and
a continuous silicide strap directly contacting the conductive element, the dielectric spacer and the semiconductor substrate.

20. The semiconductor structure of Claim 19, wherein the dielectric spacer is silicon-rich.

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D2

21. A semiconductor structure comprising:

a semiconductor substrate;
a conductive element located over the semiconductor substrate;

a dielectric spacer located adjacent to a sidewall of the conductive element;

a semiconductor region dispersed in the upper surfaces of the conductive element, the dielectric spacer and the semiconductor substrate; and

a silicide strap formed in the semiconductor region.

22. The semiconductor structure of Claim 21, wherein the dielectric spacer is silicon-rich.

23. The semiconductor structure of Claim 21, wherein the semiconductor region comprises amorphous silicon.

24. The semiconductor structure of Claim 21, wherein the semiconductor region comprises an implanted semiconductor layer.

25. The semiconductor structure of Claim 24, wherein the implanted semiconductor layer comprises silicon.--